

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

# 2SC4409

Power Amplifier Applications  
 Power switching applications

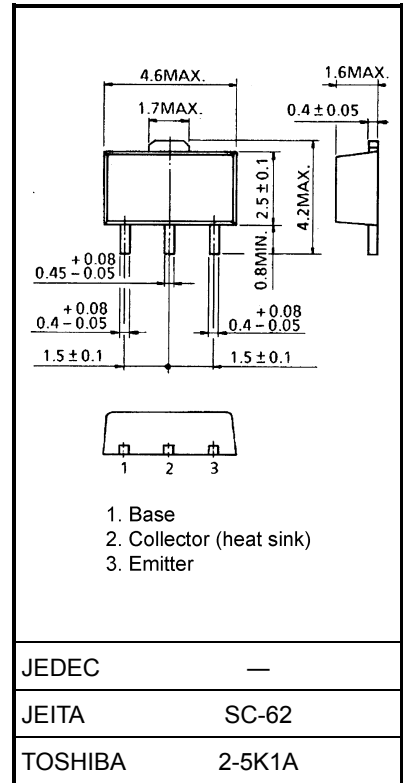
- Low collector saturation voltage:  $V_{CE(sat)} = 0.5V$  (max) (at  $I_C = 1A$ )
- High speed switching time:  $t_{stg} = 500ns$  (typ.)
- Small flat package
- $P_C = 1\text{--}2\text{ W}$  (Mounted on ceramic substrate)
- Complementary to 2SA1681

### Maximum Ratings ( $T_a = 25^\circ C$ )

| Characteristics             | Symbol       | Rating  | Unit       |
|-----------------------------|--------------|---------|------------|
| Collector-base voltage      | $V_{CBO}$    | 80      | V          |
| Collector-emitter voltage   | $V_{CEO}$    | 50      | V          |
| Emitter-base voltage        | $V_{EBO}$    | 6       | V          |
| Collector current           | $I_C$        | 2       | A          |
| Base current                | $I_B$        | 0.2     | A          |
| Collector power dissipation | $P_C$        | 500     | mW         |
| Collector power dissipation | $P_C$ (Note) | 1000    | mW         |
| Junction temperature        | $T_j$        | 150     | $^\circ C$ |
| Storage temperature range   | $T_{stg}$    | -55~150 | $^\circ C$ |

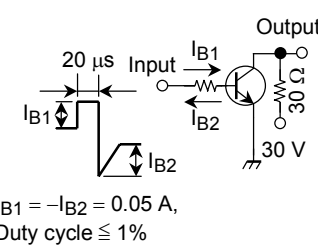
Note: 2SC4409 mounted on ceramic substrate ( $250\text{ mm}^2 \times 0.8\text{ t}$ )

Unit: mm

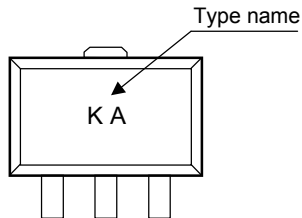


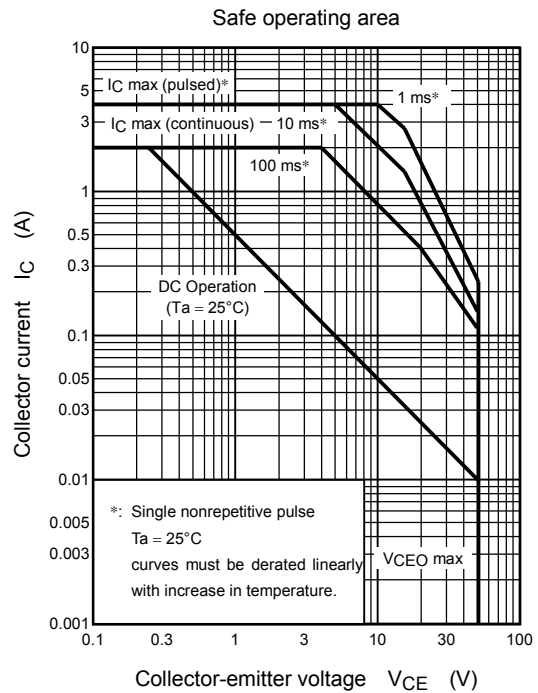
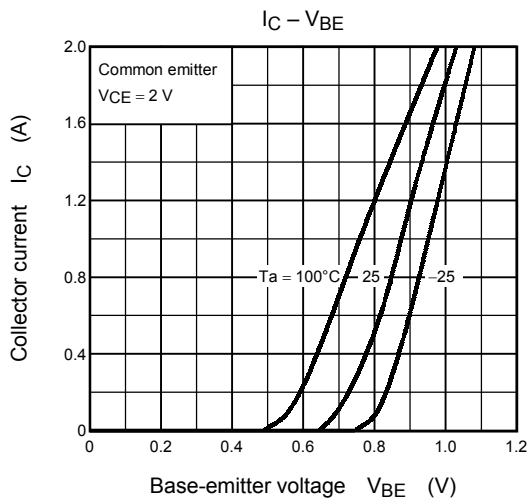
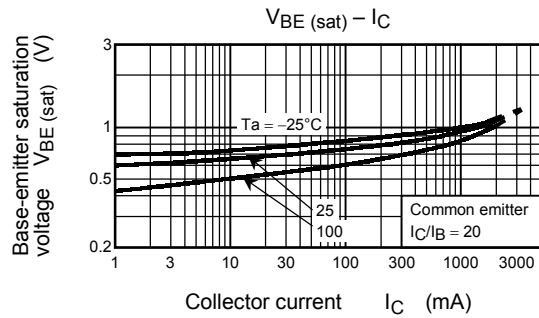
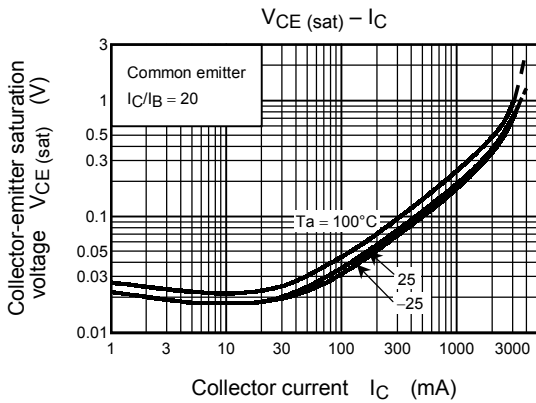
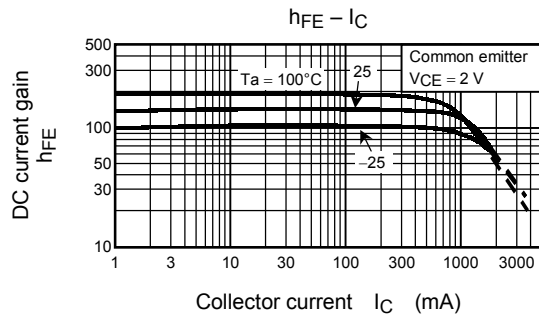
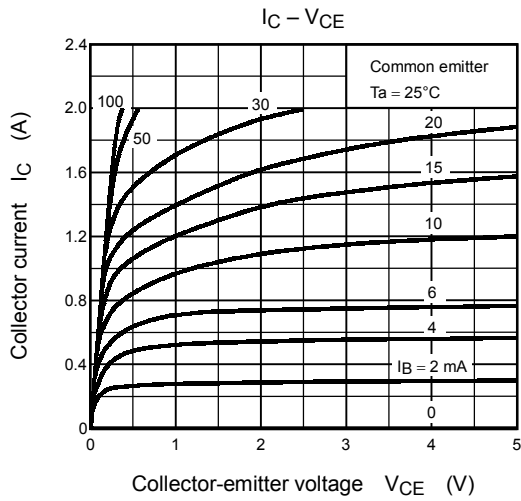
Weight: 0.05 g (typ.)

## Electrical Characteristics (Ta = 25°C)

| Characteristics                      |              | Symbol        | Test Condition  | Min | Typ. | Max | Unit          |
|--------------------------------------|--------------|---------------|---|-----|------|-----|---------------|
| Collector cut-off current            |              | $I_{CBO}$     | $V_{CB} = 80\text{ V}, I_E = 0$   | —   | —    | 0.1 | $\mu\text{A}$ |
| Emitter cut-off current              |              | $I_{EBO}$     | $V_{EB} = 6\text{ V}, I_C = 0$  | —   | —    | 0.1 | $\mu\text{A}$ |
| Collector-emitter breakdown voltage  |              | $V_{(BR)CEO}$ | $I_C = 10\text{ mA}, I_B = 0$   | 50  | —    | —   | V             |
| DC current gain                      |              | $h_{FE(1)}$   | $V_{CE} = 2\text{ V}, I_C = 100\text{ mA}$  | 120 | —    | 400 |               |
|                                      |              | $h_{FE(2)}$   | $V_{CE} = 2\text{ V}, I_C = 1.5\text{ A}$   | 40  | —    | —   |               |
| Collector-emitter saturation voltage |              | $V_{CE(sat)}$ | $I_C = 1\text{ A}, I_B = 0.05\text{ A}$   | —   | —    | 0.5 | V             |
| Base-emitter saturation voltage      |              | $V_{BE(sat)}$ | $I_C = 1\text{ A}, I_B = 0.05\text{ A}$   | —   | —    | 1.2 | V             |
| Transition frequency                 |              | $f_T$         | $V_{CE} = 2\text{ V}, I_C = 100\text{ mA}$  | —   | 100  | —   | MHz           |
| Collector output capacitance         |              | $C_{ob}$      | $V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$   | —   | 14   | —   | pF            |
| Switching time                       | Turn-on time | $t_{on}$      |  <p><math>I_{B1} = -I_{B2} = 0.05\text{ A}</math>,<br/>Duty cycle <math>\leq 1\%</math></p> | —   | 0.1  | —   | $\mu\text{s}$ |
|                                      | Storage time | $t_{stg}$     |   | —   | 0.5  | —   |               |
|                                      | Fall time    | $t_f$         |   | —   | 0.1  | —   |               |

## Marking





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